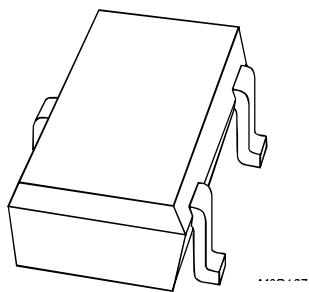


DATA SHEET



BC856W; BC857W **PNP general purpose transistors**

Product specification

1999 Apr 12

Supersedes data of 1997 Apr 07

PNP general purpose transistors**BC856W; BC857W****FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 80)
- S-mini package.

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a plastic SOT323 package.
NPN complements: BC846W and BC847W.

MARKING

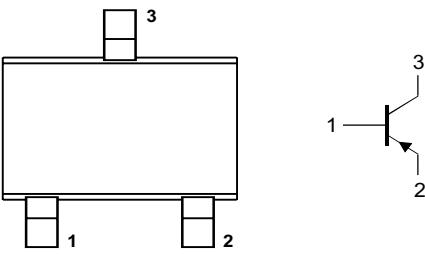
| TYPE NUMBER | MARKING CODE ⁽¹⁾ | TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|-------------|-----------------------------|
| BC856W | 3D* | BC857AW | 3E* |
| BC856AW | 3A* | BC857BW | 3F* |
| BC856BW | 3B* | BC857CW | 3G* |
| BC857W | 3H* | | |

Note

1. * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



Top view

MAM048

Fig.1 Simplified outline (SOT323) and symbol.

PNP general purpose transistors

BC856W; BC857W

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---|--|--------|------------|------------------|
| V_{CBO} | collector-base voltage BC856W BC857W | open emitter | — — | -80 -50 | V |
| V_{CEO} | collector-emitter voltage BC856W BC857W | open base | — — | -65 -45 | V |
| V_{EBO} | emitter-base voltage | open collector | — | -5 | V |
| I_C | collector current (DC) | | — | -100 | mA |
| I_{CM} | peak collector current | | — | -200 | mA |
| I_{BM} | peak base current | | — | -200 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25^\circ\text{C}$; note 1 | — | 200 | mW |
| T_{stg} | storage temperature | | -65 | +150 | $^\circ\text{C}$ |
| T_j | junction temperature | | — | 150 | $^\circ\text{C}$ |
| T_{amb} | operating ambient temperature | | -65 | +150 | $^\circ\text{C}$ |

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC856W; BC857W

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1 | 625 | K/W |

Note

- Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_{amb} = 25^\circ C$ unless otherwise specified.

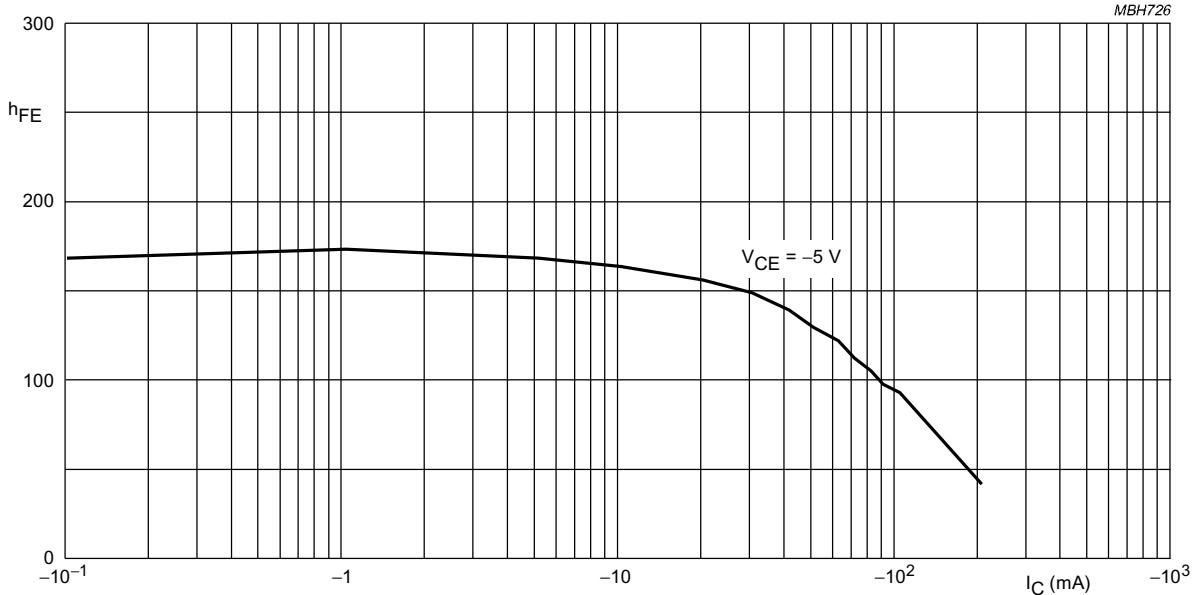
| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-------------|--|---|------|------|---------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = -30 V$ | – | -15 | nA |
| | | $I_E = 0; V_{CB} = -30 V; T_j = 150^\circ C$ | – | -4 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = -5 V$ | – | -100 | nA |
| h_{FE} | DC current gain BC856W BC857W BC856AW; BC857AW BC856BW; BC857BW BC857CW | $I_C = -2 mA; V_{CE} = -5 V;$ see Figs 2, 3 and 4 | 125 | 475 | |
| | | | 125 | 800 | |
| | | | 125 | 250 | |
| | | | 220 | 475 | |
| | | | 420 | 800 | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = -10 mA; I_B = -0.5 mA$ | – | -300 | mV |
| | | $I_C = -100 mA; I_B = -5 mA; \text{note 1}$ | – | -650 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = -100 mA; I_B = -5 mA; \text{note 1}$ | – | -950 | mV |
| V_{BE} | base-emitter voltage | $I_C = -2 mA; V_{CE} = -5 V$ | -600 | -750 | mV |
| | | $I_C = -10 mA; V_{CE} = -5 V$ | – | -820 | mV |
| C_c | collector capacitance | $I_E = i_e = 0; V_{CB} = -10 V; f = 1 MHz$ | – | 5 | pF |
| C_e | emitter capacitance | $I_C = i_c = 0; V_{EB} = -0.5 V; f = 1 MHz$ | – | 12 | pF |
| f_T | transition frequency | $I_C = -10 mA; V_{CE} = -5 V; f = 100 MHz$ | 100 | – | MHz |
| F | noise figure | $I_C = -200 \mu A; V_{CE} = -5 V; R_S = 2 k\Omega; f = 1 kHz; B = 200 Hz$ | – | 10 | dB |

Note

- Pulse test: $t_p \leq 300 \mu s; \delta \leq 0.02$.

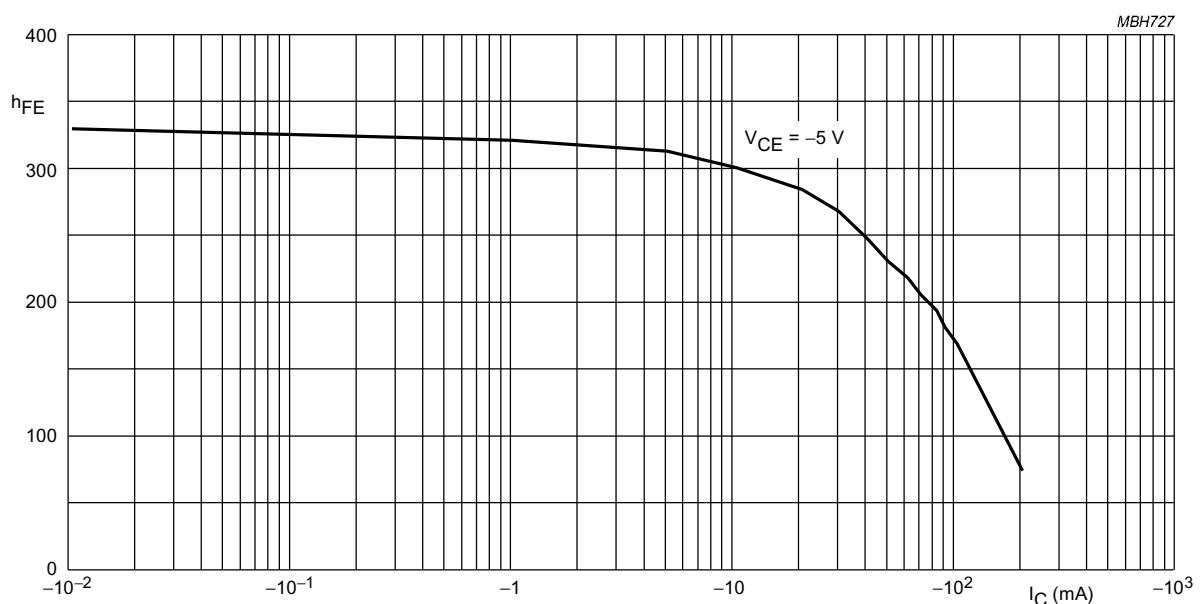
PNP general purpose transistors

BC856W; BC857W



BC856AW; BC857AW.

Fig.2 DC current gain; typical values.

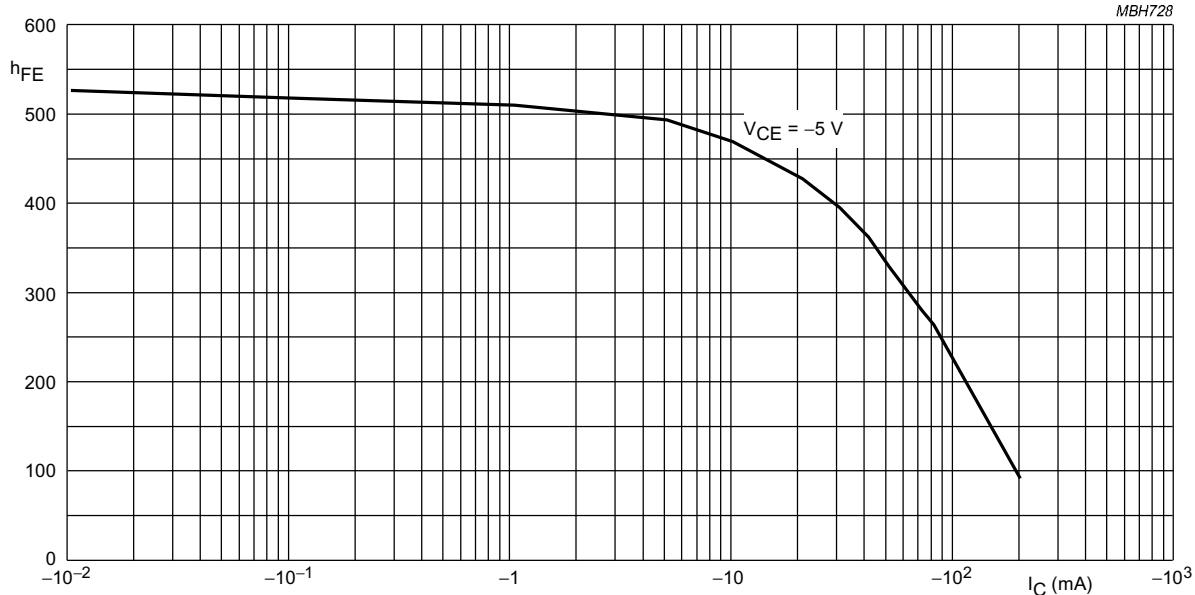


BC856BW; BC857BW.

Fig.3 DC current gain; typical values.

PNP general purpose transistors

BC856W; BC857W



BC857CW.

Fig.4 DC current gain; typical values.

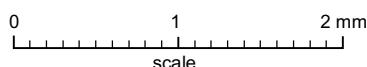
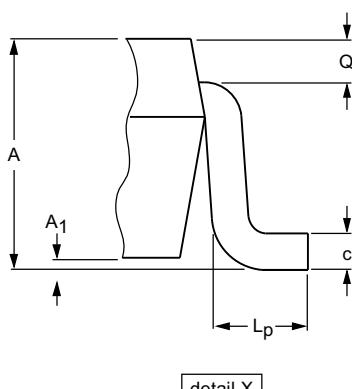
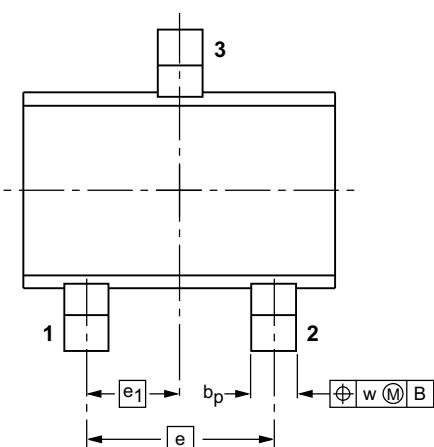
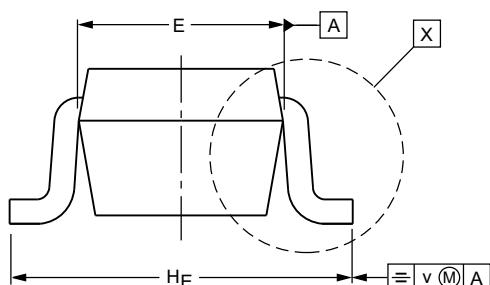
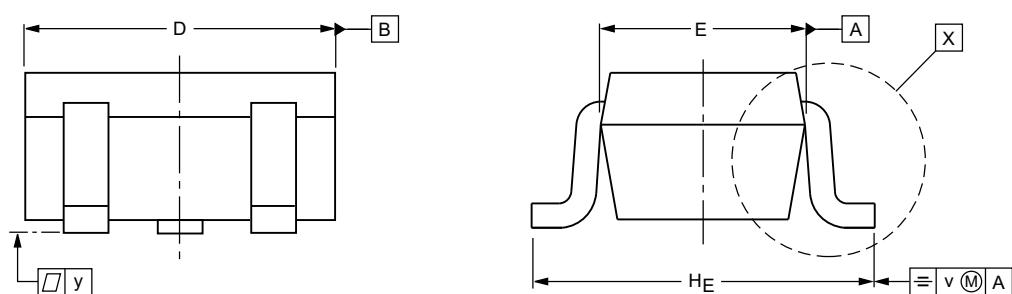
PNP general purpose transistors

BC856W; BC857W

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A_1 max | b_p | c | D | E | e | e_1 | H_E | L_p | Q | v | w |
|------|------------|--------------|------------|--------------|------------|--------------|-----|-------|------------|--------------|--------------|-----|-----|
| mm | 1.1 0.8 | 0.1 | 0.4 0.3 | 0.25 0.10 | 2.2 1.8 | 1.35 1.15 | 1.3 | 0.65 | 2.2 2.0 | 0.45 0.15 | 0.23 0.13 | 0.2 | 0.2 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|------|-------|------------------------|------------|
| | IEC | JEDEC | EIAJ | SC-70 | | |
| SOT323 | | | | | | 97-02-28 |

PNP general purpose transistors**BC856W; BC857W****DEFINITIONS**

| Data sheet status | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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PNP general purpose transistors

BC856W; BC857W

NOTES

PNP general purpose transistors

BC856W; BC857W

NOTES

PNP general purpose transistors

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NOTES

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